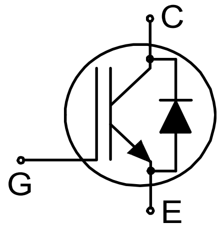
TRENCHSTOP™ RC-Drives Fast Series

IGBT with integrated diode in packages offering space saving advantage



Features:

TRENCHSTOP™ Reverse Conducting (RC) technology for 600V applications offering

- Optimized Eon, Eoff and Qrr for low switching losses
- Operating range of 4 to 30kHz
- Smooth switching performance leading to low EMI levels
- Very tight parameter distribution
- Maximum junction temperature 175°C
- Dynamically stress tested
- Short circuit capability of 5µs
- Best in class current versus package size performance
- Qualified according to AEC-Q101
- Pb-free lead plating; RoHS compliant (solder temperature 260°C, MSL1)

Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/

Applications:

- Small drives
- Piezo injection
- Automotive lighting / HID

Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
AIHD03N60RF	600V	2.5A	2.2V	175°C	AH03DRF	PG-TO252-3

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Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25°C$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_C = 25°C$ $T_C = 100°C$	I_C	 6.5 6.0	A
Pulsed collector current, t_p limited by T_{vjmax}[1)]	I_{Cpuls}	7.5	A
Turn off safe operating area $V_{CE} \leq 600V$, $T_{vj} \leq 175°C$, $t_p = 1µs$[1)]	-	7.5	A
Diode forward current, limited by T_{vjmax} $T_C = 25°C$ $T_C = 100°C$	I_F	 6.3 3.9	A
Diode pulsed current, t_p limited by T_{vjmax}[1)]	I_{Fpuls}	7.5	A
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time $V_{GE} = 15.0V$, $V_{CC} \leq 400V$ Allowed number of short circuits < 1000 Time between short circuits: ≥ 1.0s $T_{vj} = 150°C$	t_{SC}	 5	µs
Power dissipation $T_C = 25°C$	P_{tot}	53.6	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STA-020)		 260	°C

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R_{th} Characteristics						
IGBT thermal resistance,[2)] junction - case	$R_{th(j-c)}$		-	-	2.80	K/W
Diode thermal resistance,[3)] junction - case	$R_{th(j-c)}$		-	-	6.80	K/W
Thermal resistance, min. footprint junction - ambient	$R_{th(j-a)}$		-	-	75	K/W
Thermal resistance, 6cm² Cu on PCB junction - ambient	$R_{th(j-a)}$		-	-	50	K/W

1) Defined by design. Not subject to production test.
2) Rth/Zth based on single cooling pulse. Please be aware that a correct Rth measurement of the IGBT, is not possible using a thermocouple.
3) Rth/Zth based on single cooling pulse. Please be aware that a correct Rth measurement of the Diode, is not possible using a thermocouple.

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 0.20mA	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 2.5A T_{vj} = 25°C T_{vj} = 175°C	 - -	 2.20 2.30	 2.50 -	V
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 2.5A T_{vj} = 25°C T_{vj} = 175°C	 - -	 2.10 2.00	 2.40 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 0.05mA, V_{CE} = V_{GE}	4.3	5.0	5.7	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 600V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 175°C	 - -	 - 120	 40 -	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance[1]	g_{fs}	V_{CE} = 10V, I_C = 2.5A	-	1.3	-	S
Integrated gate resistor	r_G			none		Ω

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	200	-	pF
Output capacitance	C_{oes}		-	13	-	
Reverse transfer capacitance	C_{res}		-	7	-	
Gate charge	Q_G	V_{CC} = 480V, I_C = 2.5A, V_{GE} = 15V	-	17.1	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: ≥ 1.0s	$I_{C(SC)}$	V_{GE} = 15.0V, V_{CC} ≤ 400V, t_{SC} ≤ 5µs T_{vj} = 25°C	-	23	-	A

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 25°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 2.5A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 68.0Ω, $R_{G(off)}$ = 68.0Ω, $L\sigma$ = 60nH, $C\sigma$ = 40pF $L\sigma$, $C\sigma$ from Fig. E	-	10	-	ns
Rise time	t_r		-	8	-	ns
Turn-off delay time	$t_{d(off)}$		-	128	-	ns
Fall time	t_f		-	93	-	ns
Turn-on energy	E_{on}		-	0.05	-	mJ
Turn-off energy	E_{off}		-	0.04	-	mJ
Total switching energy	E_{ts}		-	0.09	-	mJ

[1] Typical value of transconductance determined at T_{vj}=175°C.

Diode Characteristic, at T_{vj} = 25°C

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 2.5A, di_F/dt = 470A/µs	-	31	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.06	-	µC
Diode peak reverse recovery current	I_{rrm}		-	3.8	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-196	-	A/µs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 175°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 175°C, V_{CC} = 400V, I_C = 2.5A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 68.0Ω, $R_{G(off)}$ = 68.0Ω, $L\sigma$ = 60nH, $C\sigma$ = 40pF $L\sigma$, $C\sigma$ from Fig. E	-	9	-	ns
Rise time	t_r		-	9	-	ns
Turn-off delay time	$t_{d(off)}$		-	142	-	ns
Fall time	t_f		-	123	-	ns
Turn-on energy	E_{on}		-	0.08	-	mJ
Turn-off energy	E_{off}		-	0.06	-	mJ
Total switching energy	E_{ts}		-	0.14	-	mJ

Diode Characteristic, at T_{vj} = 175°C

Diode reverse recovery time	t_{rr}	T_{vj} = 175°C, V_R = 400V, I_F = 2.5A, di_F/dt = 470A/µs	-	66	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.19	-	µC
Diode peak reverse recovery current	I_{rrm}		-	6.2	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-125	-	A/µs

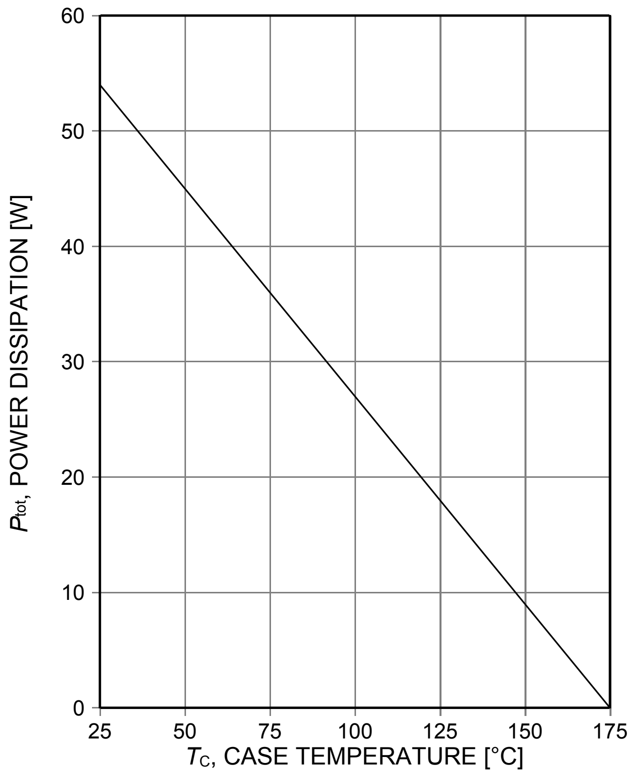


Figure 1. **Power dissipation as a function of case temperature**
(T_{vj}≤175°C)

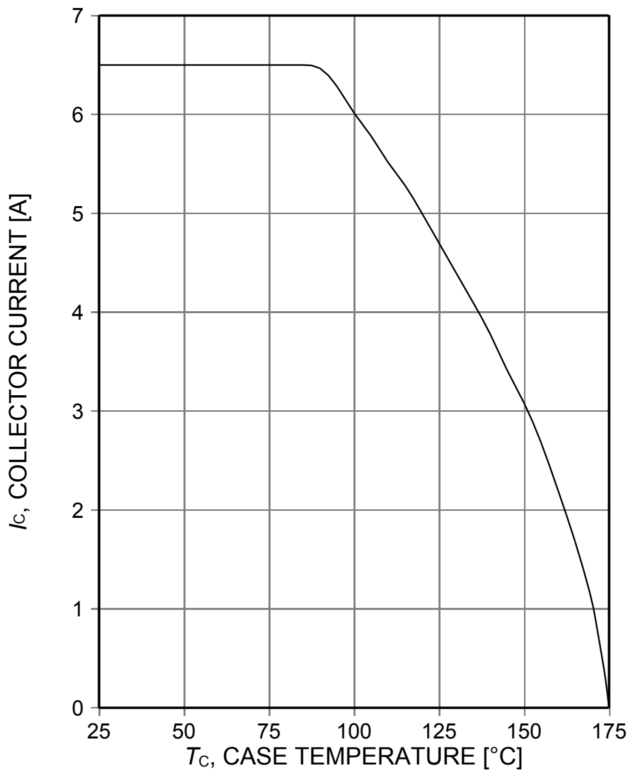


Figure 2. **Collector current as a function of case temperature**
(V_{GE}≥15V, T_{vj}≤175°C)

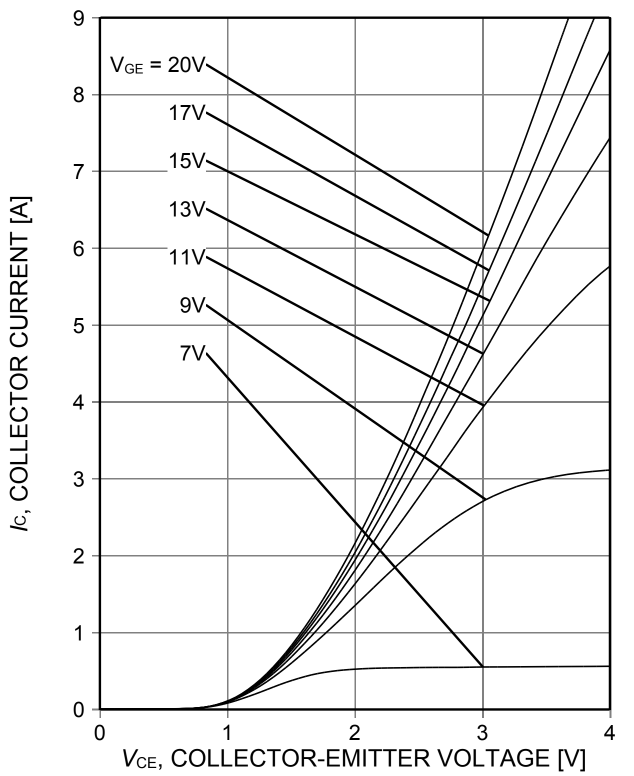


Figure 3. **Typical output characteristic**
(T_{vj}=25°C)

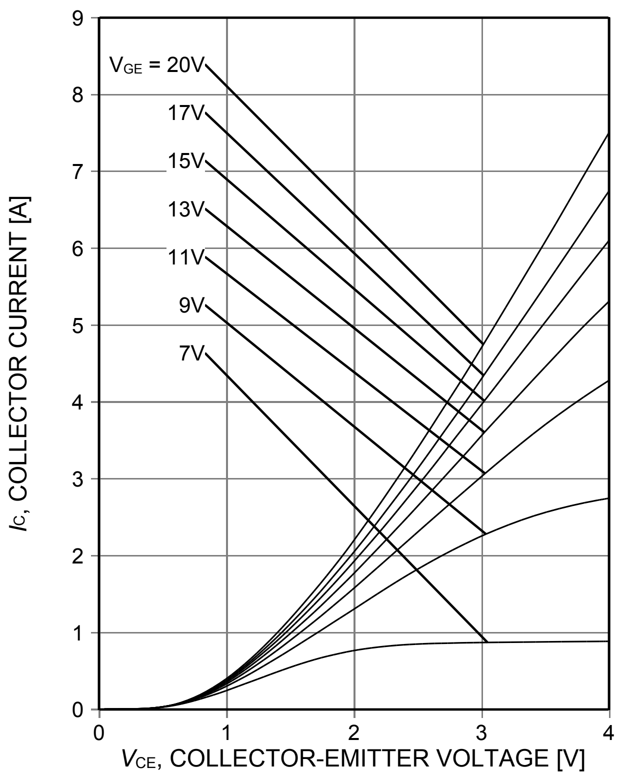


Figure 4. **Typical output characteristic**
(T_{vj}=175°C)

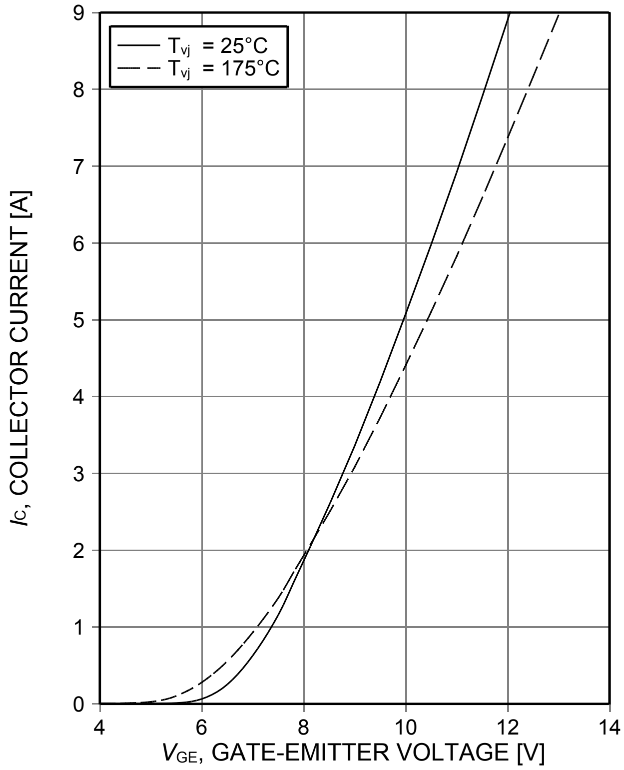


Figure 5. **Typical transfer characteristic** (V_{CE}=10V)

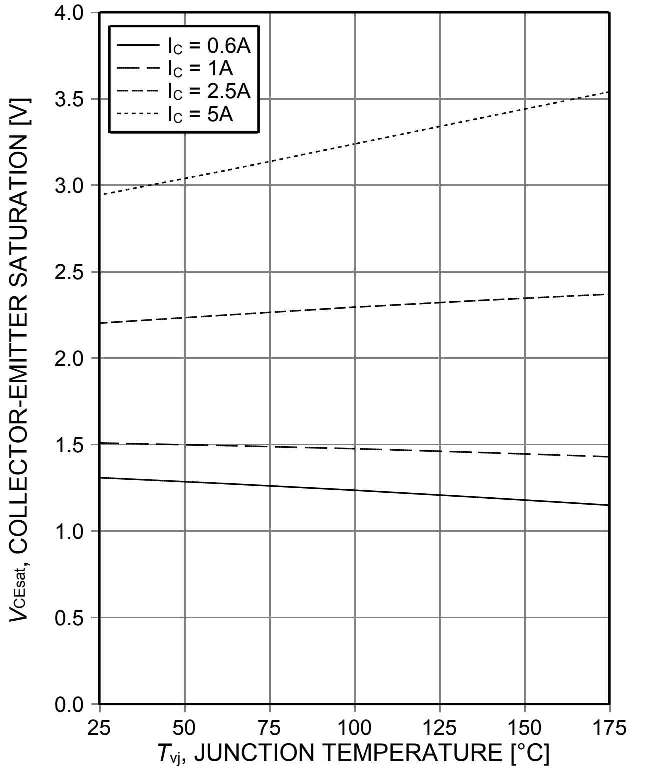


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature** (V_{GE}=15V)

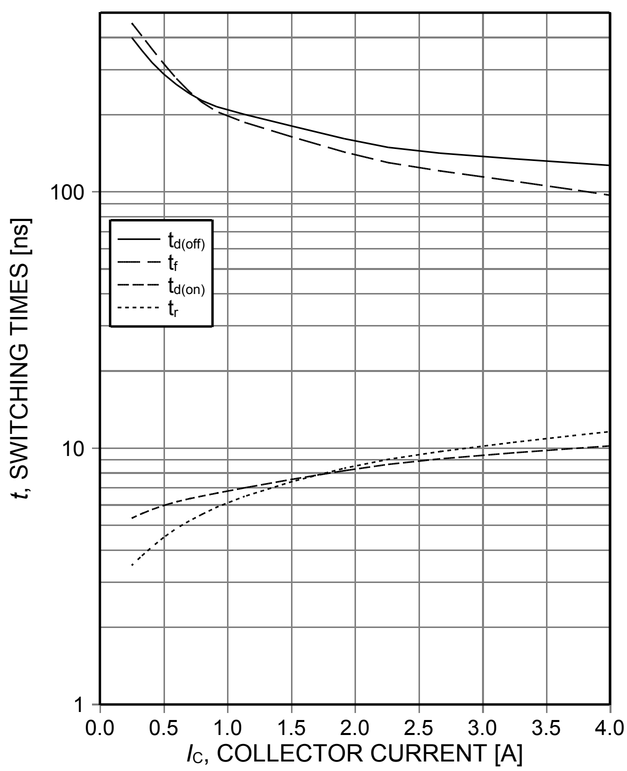


Figure 7. **Typical switching times as a function of collector current** (inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15V, R_{Gon}=68Ω, R_{Goff}=68Ω, dynamic test circuit in Figure E)

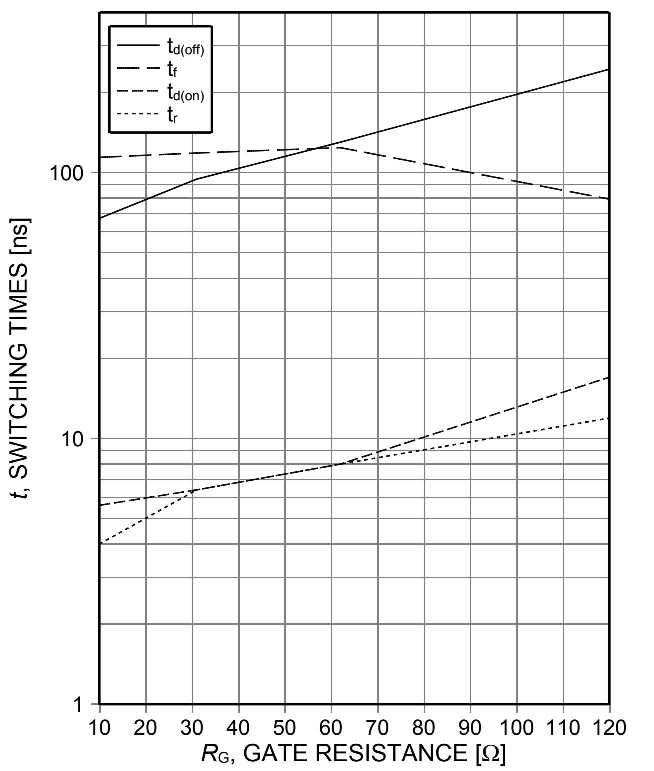


Figure 8. **Typical switching times as a function of gate resistance** (inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15V, I_C=2,5A, dynamic test circuit in Figure E)

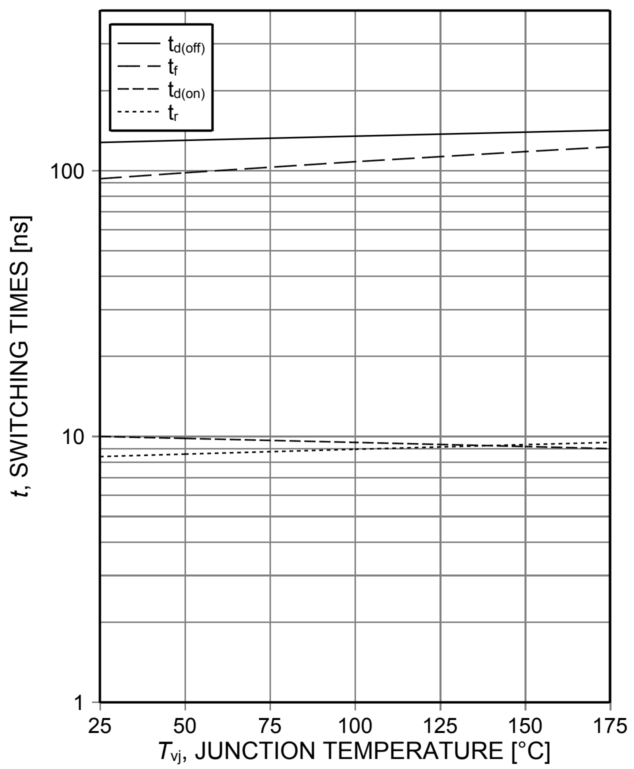


Figure 9. **Typical switching times as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=2,5A, R_{Gon}=68Ω, R_{Goff}=68Ω, dynamic test circuit in Figure E)

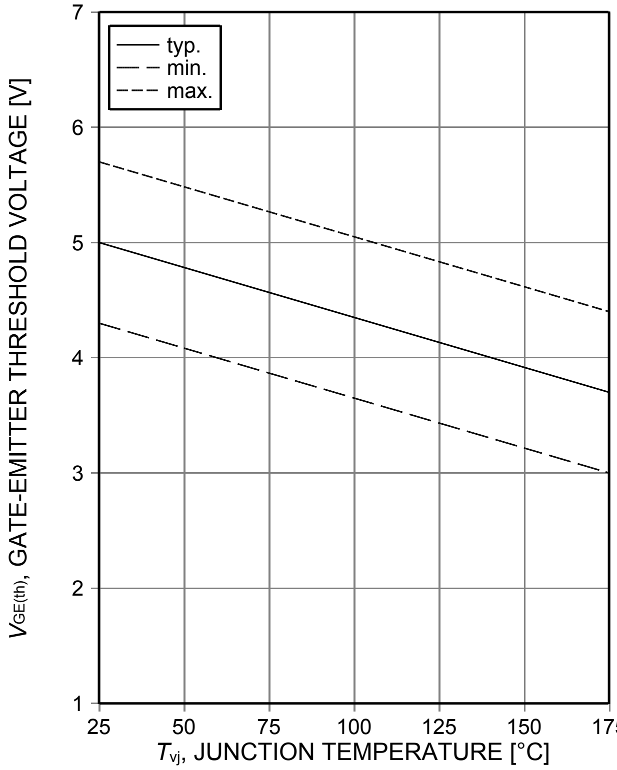


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
(I_C=0,05mA)

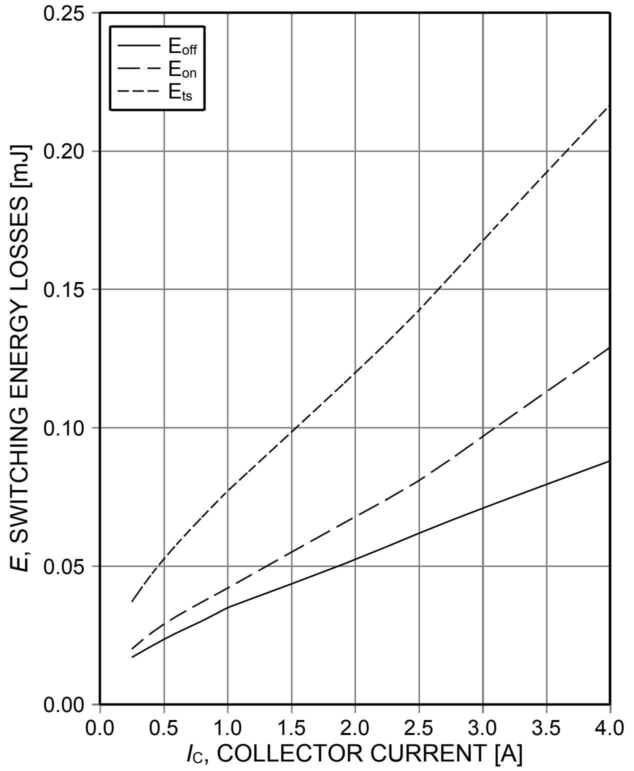


Figure 11. **Typical switching energy losses as a function of collector current**
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15V, R_{Gon}=68Ω, R_{Goff}=68Ω, dynamic test circuit in Figure E)

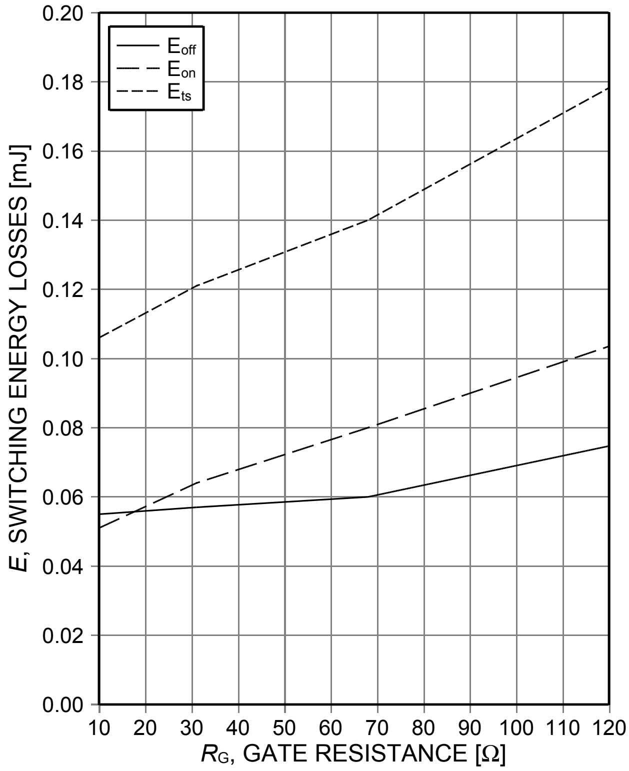


Figure 12. **Typical switching energy losses as a function of gate resistance**
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15V, I_C=2,5A, dynamic test circuit in Figure E)

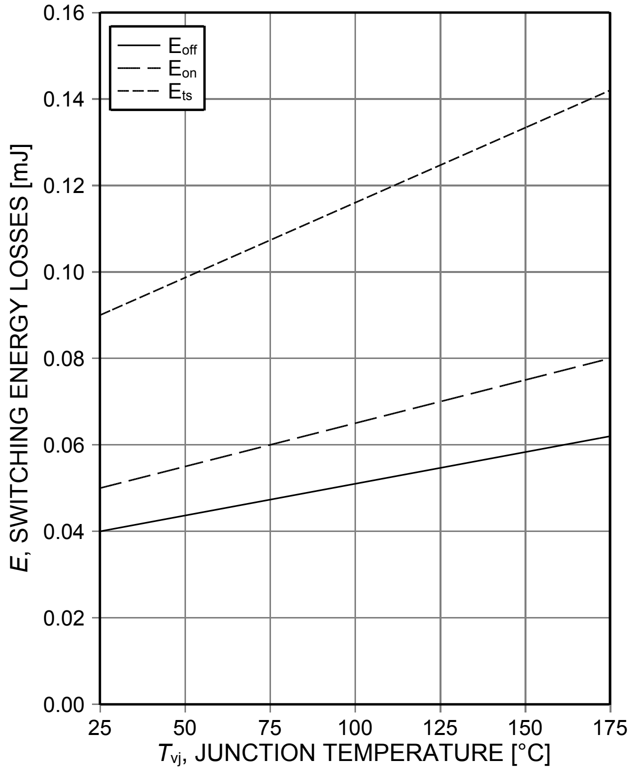


Figure 13. **Typical switching energy losses as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=2,5A, R_{Gon}=68Ω, R_{Goff}=68Ω, dynamic test circuit in Figure E)

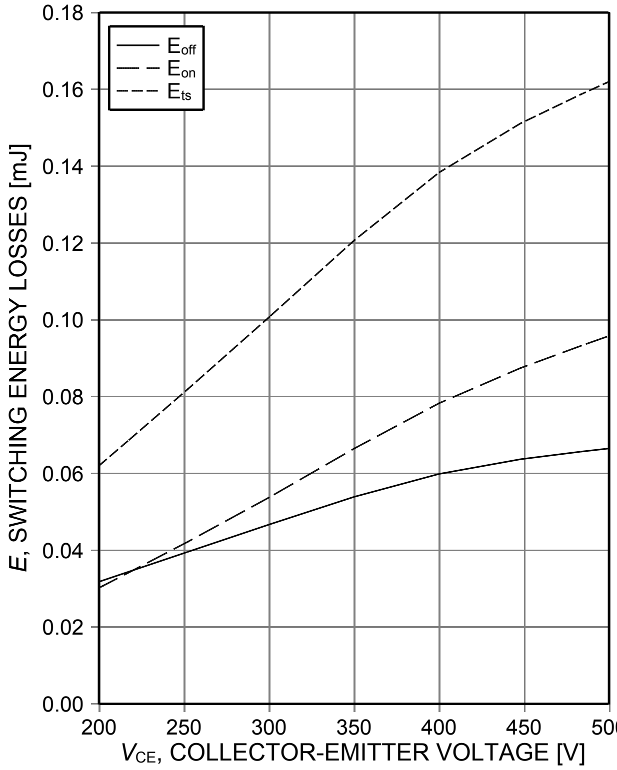


Figure 14. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, T_{vj}=175°C, V_{GE}=0/15V, I_C=2,5A, R_{Gon}=68Ω, R_{Goff}=68Ω, dynamic test circuit in Figure E)

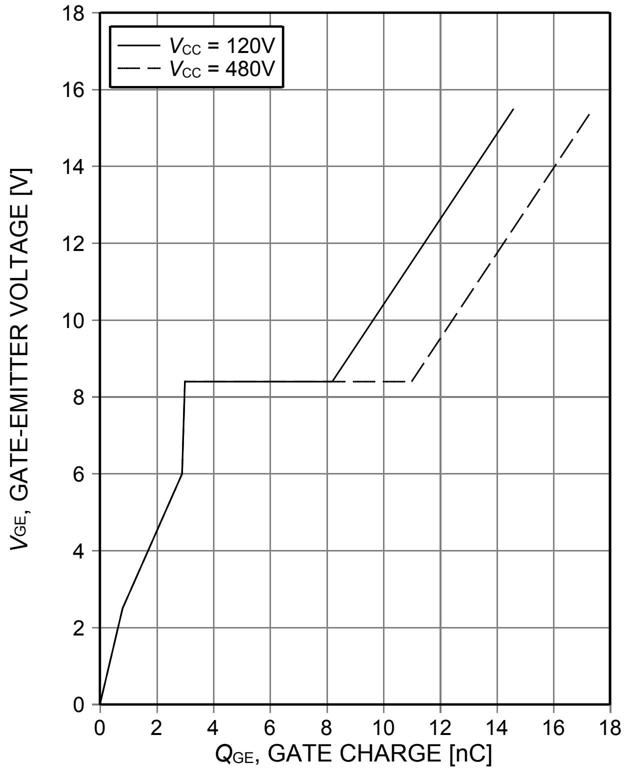


Figure 15. **Typical gate charge**
(I_C=2,5A)

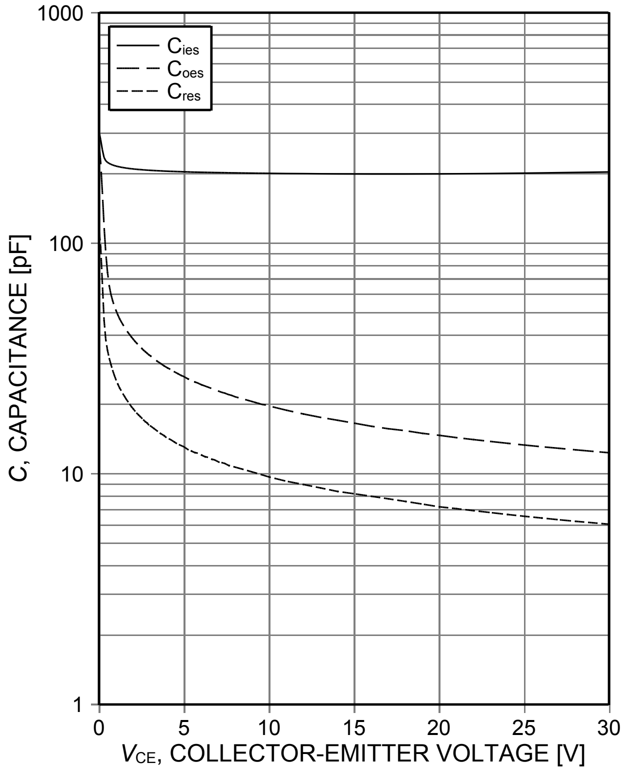


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
(V_{GE}=0V, f=1MHz)

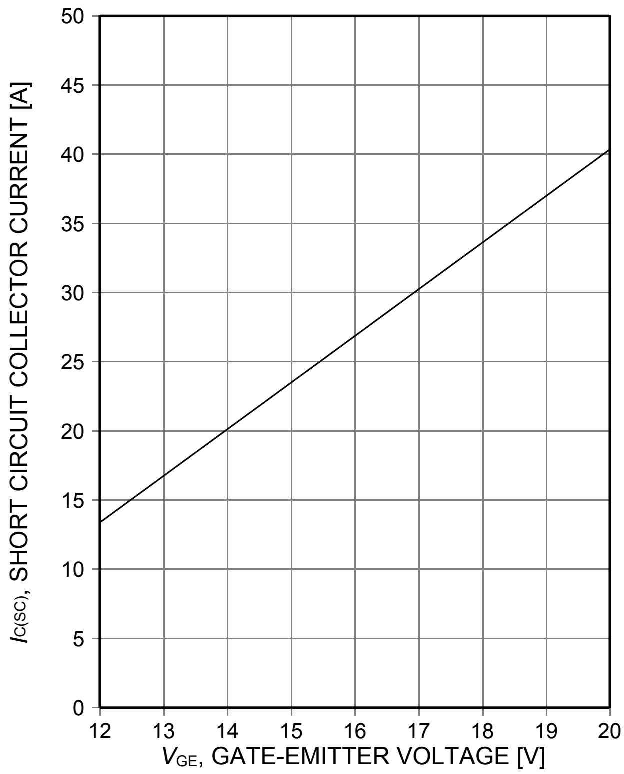


Figure 17. **Typical short circuit collector current as a function of gate-emitter voltage**
(V_{CE}≤400V, start at T_{vj}=25°C)

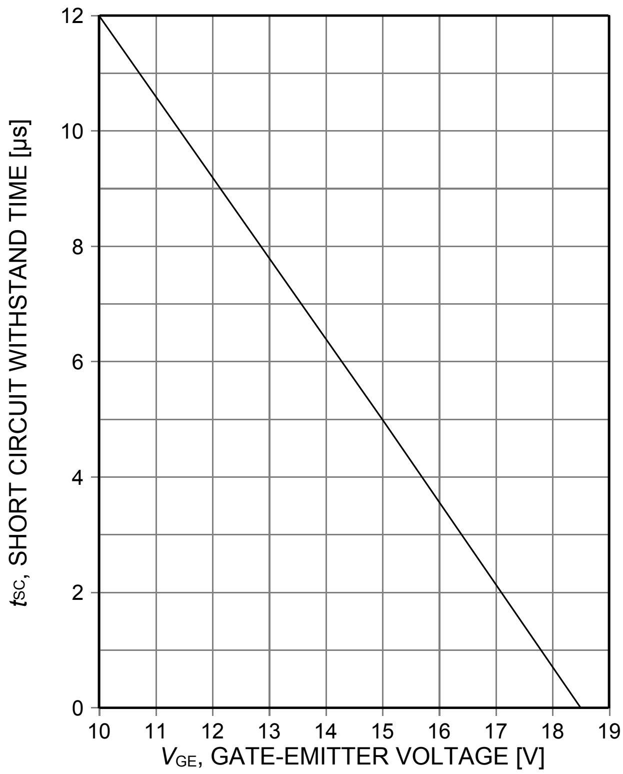
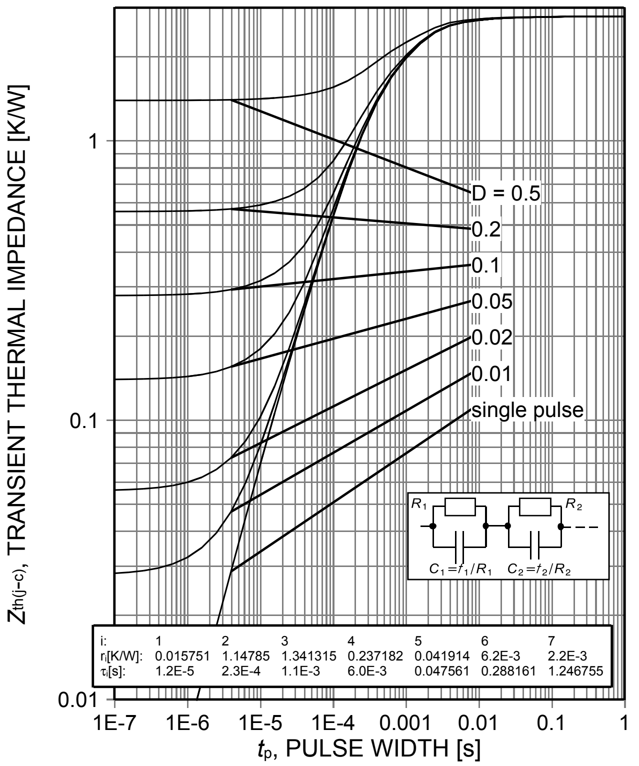
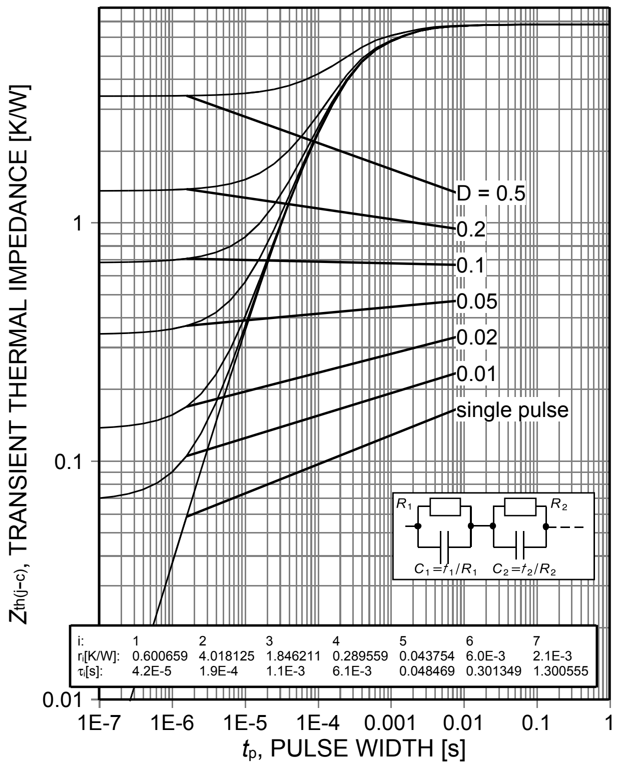


Figure 18. **Short circuit withstand time as a function of gate-emitter voltage**
(V_{CE}≤400V, start at T_{vj}=150°C)



i:	1	2	3	4	5	6	7
r_i[K/W]:	0.015751	1.14785	1.341315	0.237182	0.041914	6.2E-3	2.2E-3
τ_i[s]:	1.2E-5	2.3E-4	1.1E-3	6.0E-3	0.047561	0.288161	1.246755

Figure 19. **IGBT transient thermal impedance as a function of pulse width (see page 4 [2)])**
(D=t_p/T)



i:	1	2	3	4	5	6	7
r_i[K/W]:	0.600659	4.018125	1.846211	0.289559	0.043754	6.0E-3	2.1E-3
τ_i[s]:	4.2E-5	1.9E-4	1.1E-3	6.1E-3	0.048469	0.301349	1.300555

Figure 20. **Diode transient thermal impedance as a function of pulse width (see page 4 [3)])**
(D=t_p/T)

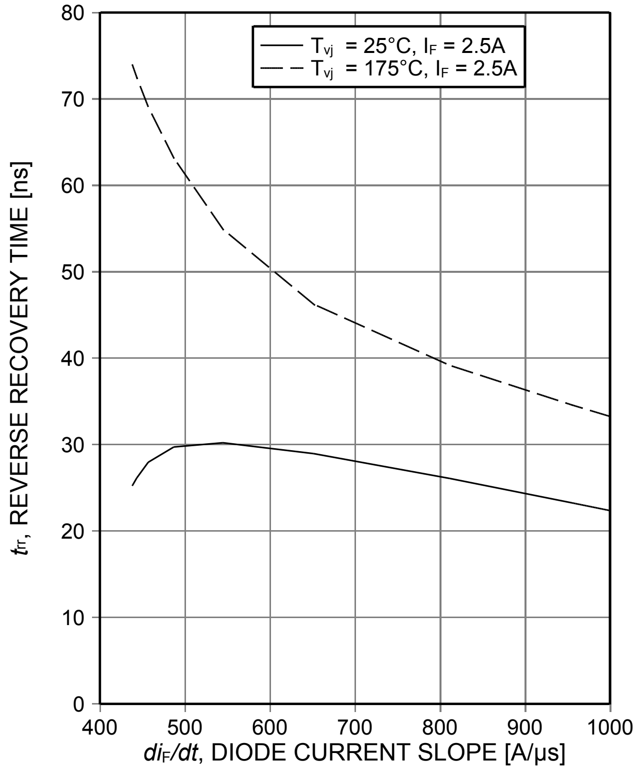


Figure 21. **Typical reverse recovery time as a function of diode current slope**
(V_R=400V)

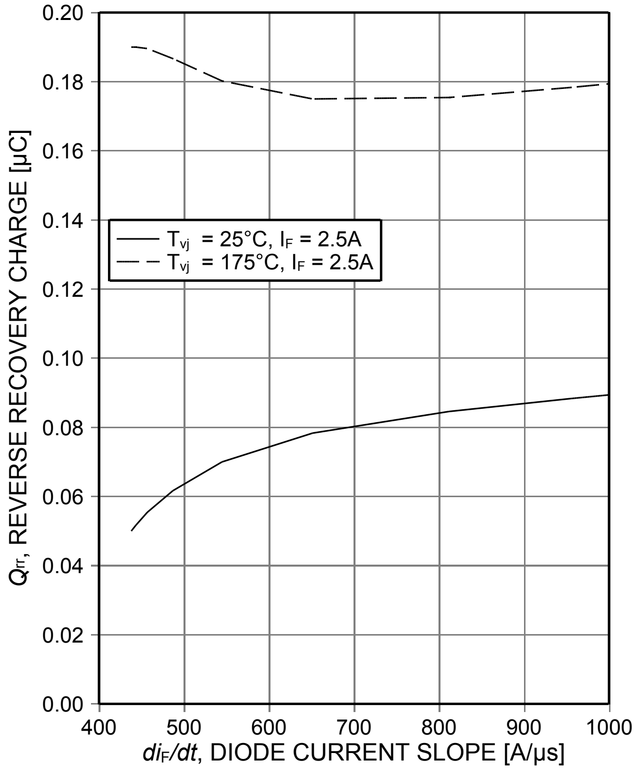


Figure 22. **Typical reverse recovery charge as a function of diode current slope**
(V_R=400V)

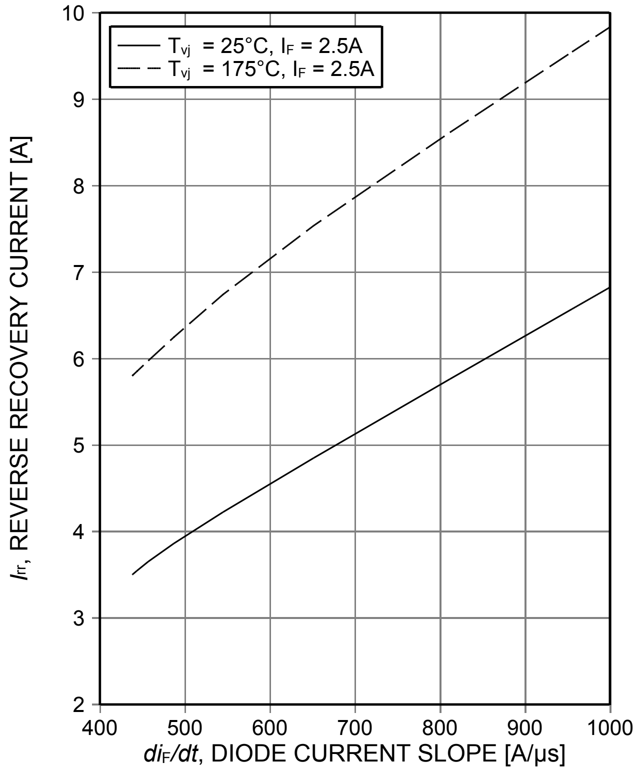


Figure 23. **Typical reverse recovery current as a function of diode current slope**
(V_R=400V)

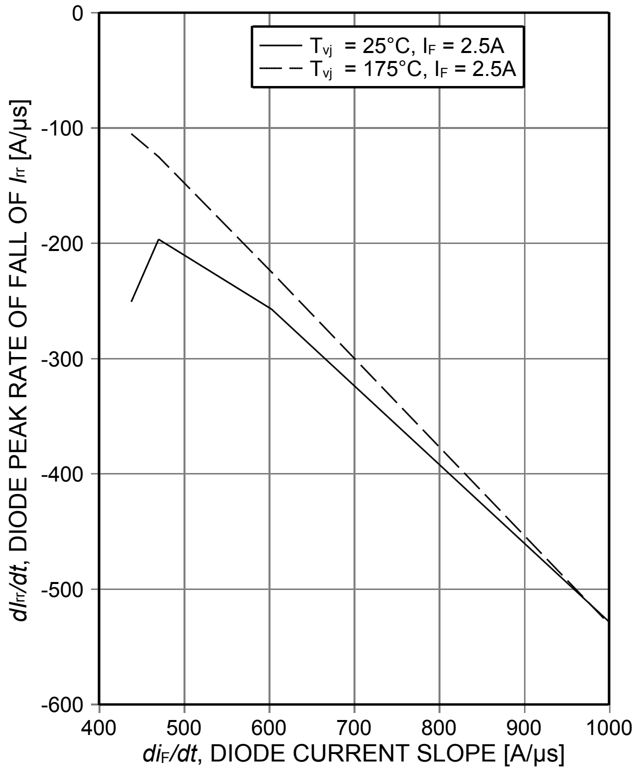


Figure 24. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
(V_R=400V)

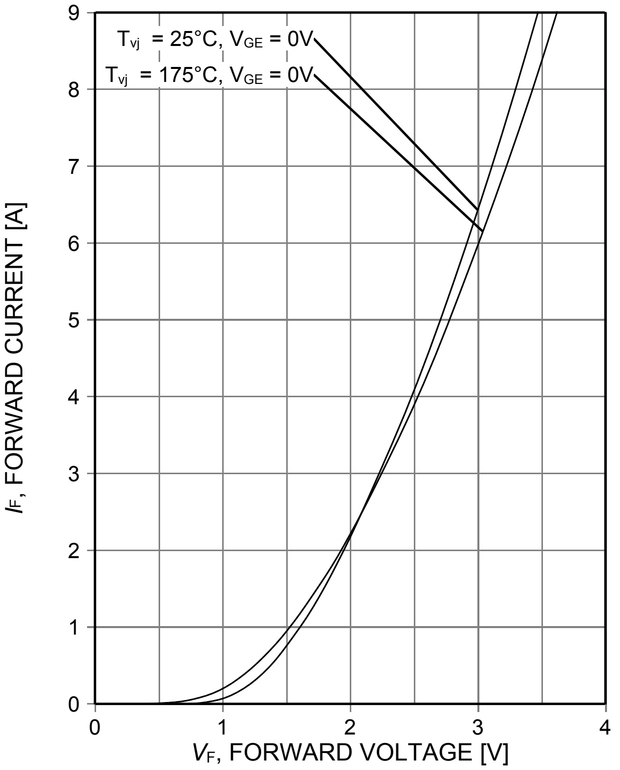


Figure 25. **Typical diode forward current as a function of forward voltage**

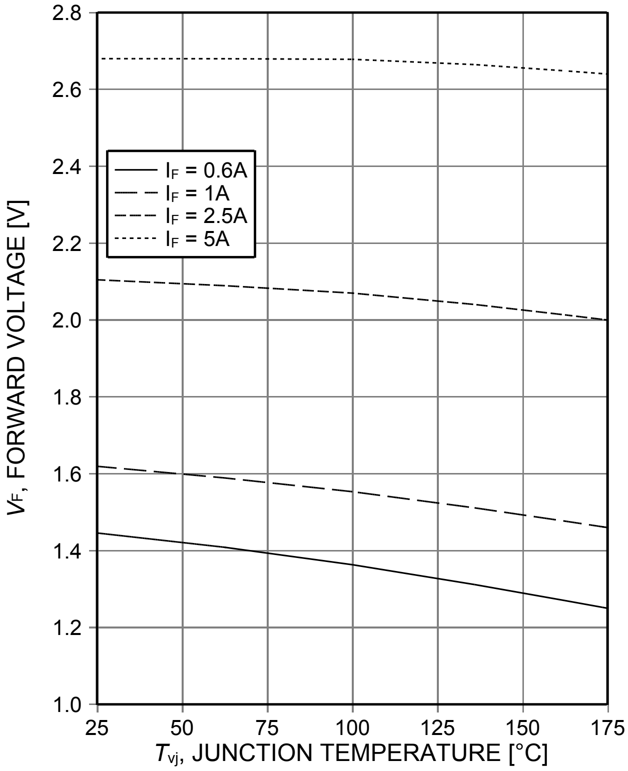
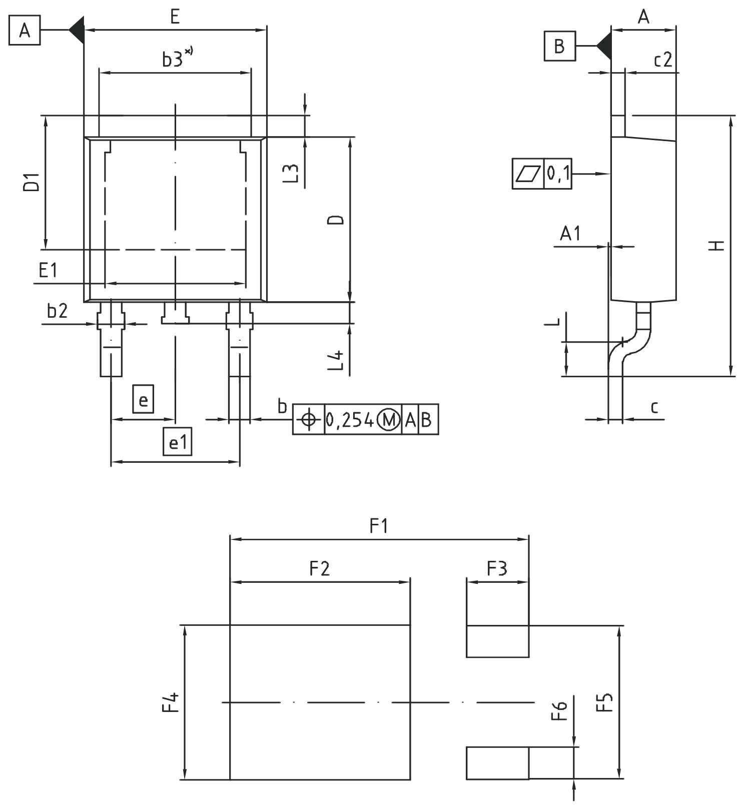


Figure 26. **Typical diode forward voltage as a function of junction temperature**

Package Drawing PG-TO252-3



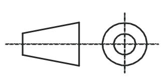
*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

DOCUMENT NO.
Z8B00003328

SCALE
0
2.0
0 2.0
4mm

EUROPEAN PROJECTION



ISSUE DATE
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REVISION
04

Testing Conditions

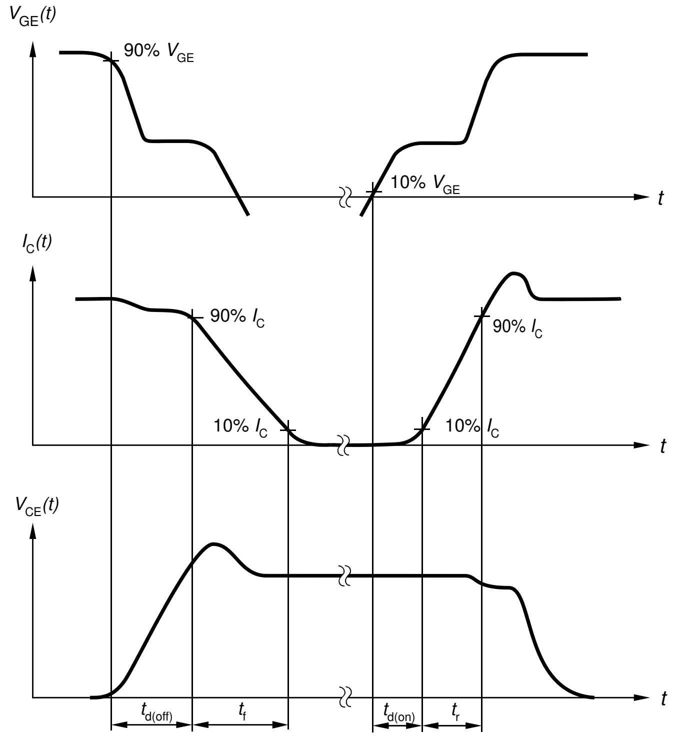

Figure A. **Definition of switching times**

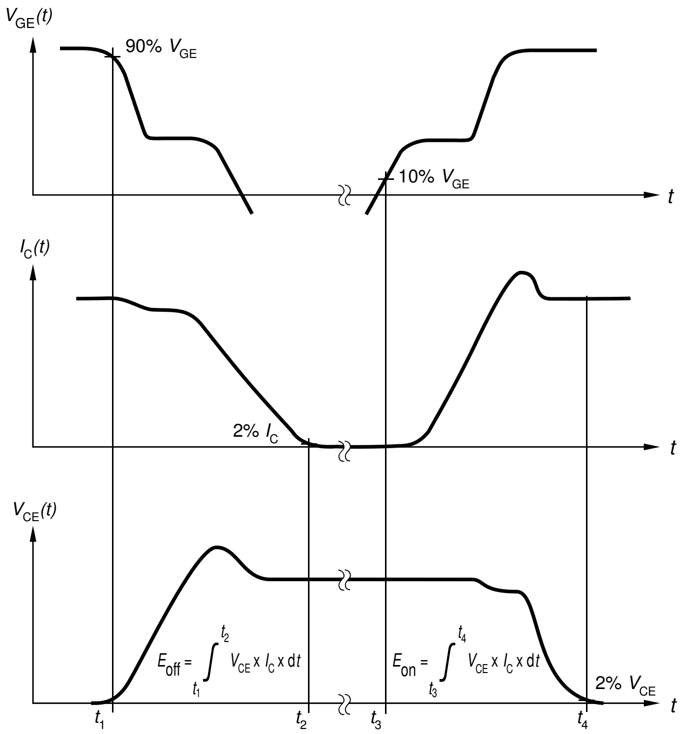

Figure B. **Definition of switching losses**

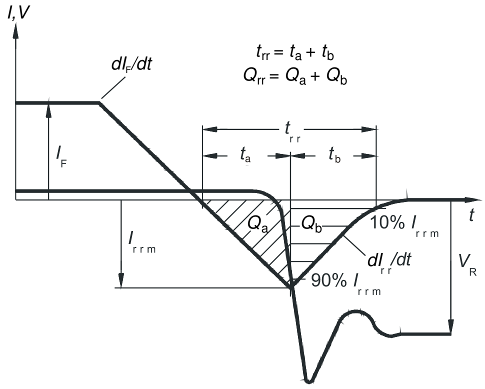

Figure C. **Definition of diode switching characteristics**

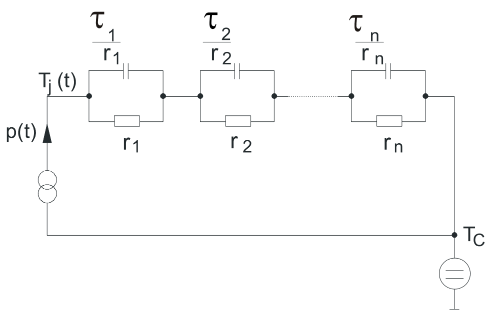

Figure D. **Thermal equivalent circuit**

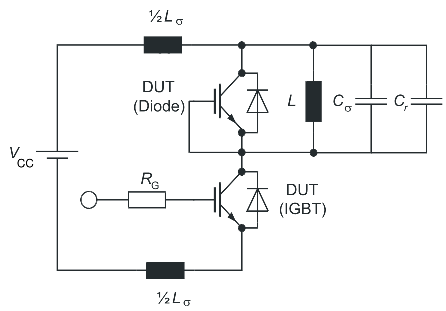

Figure E. **Dynamic test circuit**
Parasitic inductance L_{σ},
parasitic capacitor C_{σ},
relief capacitor C_r,
(only for ZVT switching)

Revision History

AIHD03N60RF

Revision: 2017-02-09, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2017-02-09	Data sheet created

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